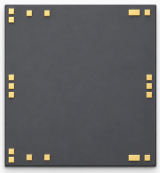
8000–18000 MHz GaN MMIC Power Amplifier Die

LCI-PA-8000-18000-PS44T is a GaN MMIC power amplifier supplied as bare die for 8000–18000 MHz. It supports CW and pulsed operation.

The RF table specifies: Saturated output power: 44 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 30 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.2 V. Die dimensions: 3.5 × 4 × 0.1 mm.



RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	8000	-	18000	MHz
Saturated output power	Psat	-	44	-	dBm
Power gain	Gp	-	19	-	dB
Power-gain flatness	ΔGp	-	-	±0.5	dB
Power-added efficiency	PAE	-	30	-	%
Small-signal gain	S21	-	33	-	dB
Small-signal gain flatness	ΔS21	-	-	±1	dB
Input VSWR	VSWR(in)	-	1.4	2	-

DC bias and current

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Drain voltage	Vd	-	28	32	V
Gate voltage	Vg	-2.8	-2.2	-1.8	V
Quiescent drain current	Id	-	2	-	A
Dynamic drain current	Idd	-	3.8	4.1	A
Dynamic gate current	Igg	-	0.2	1	mA

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	32	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	27	dBm
Maximum channel temperature	Top	-	-	225	°C
Storage temperature	TSTG	-65	-	150	°C

Die dimensions

Parameter	Value	Unit
Die dimensions	3.5 × 4 × 0.1	mm
Plan-view outline tolerance	±100 (Plan-view outline only; the source does not specify thickness tolerance.)	µm

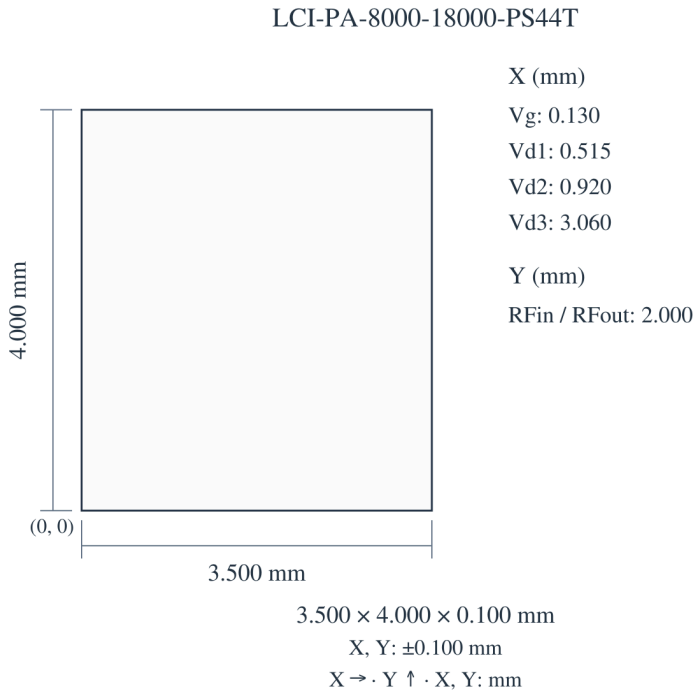
Current publication record · 1.7 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.6.

Die integration and bias sequencing

Apply gate bias before drain bias at power-up. At power-down, remove drain bias before gate bias. Use clean handling, ESD protection and a carrier with thermal expansion compatible with the SiC die.

Mechanical Outline

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.

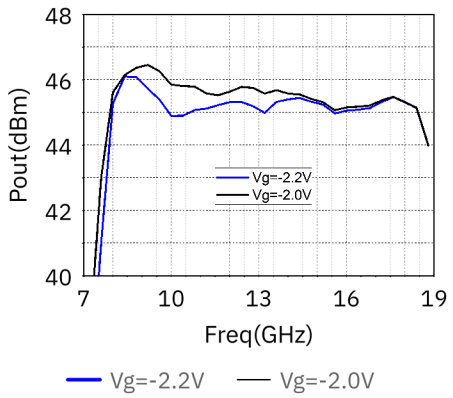


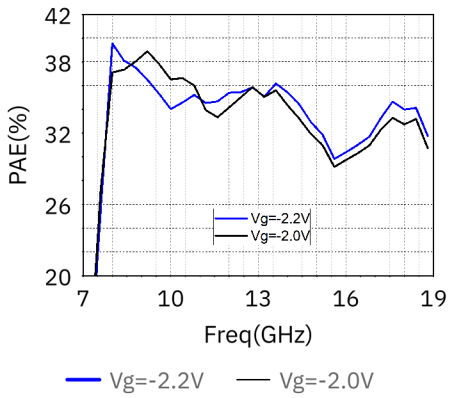
Performance curves

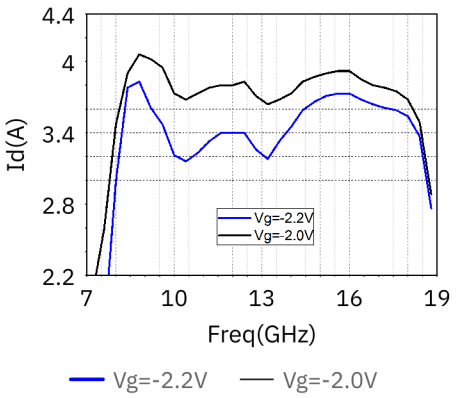
Each performance plot applies to its stated operating conditions.

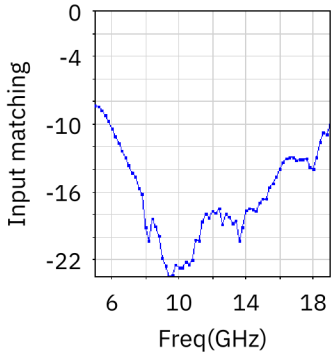
Pulsed — Saturated output power; Power-added efficiency; Dynamic drain current; Input matching; Gain.

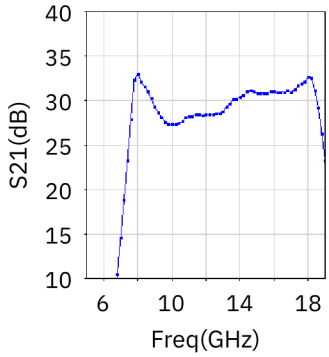
Figure notes: TA=+25°C; Vd=+28V. PW = 100 µs; D = 10%. Plots 1–3: Pin = 25 dBm. Plots 4–5: Pin = -10 dBm. The input-matching plot shows negative values on its vertical axis, with no specified unit or S11 designation. Plots 1–3: Vg = -2.2/-2.0 V.





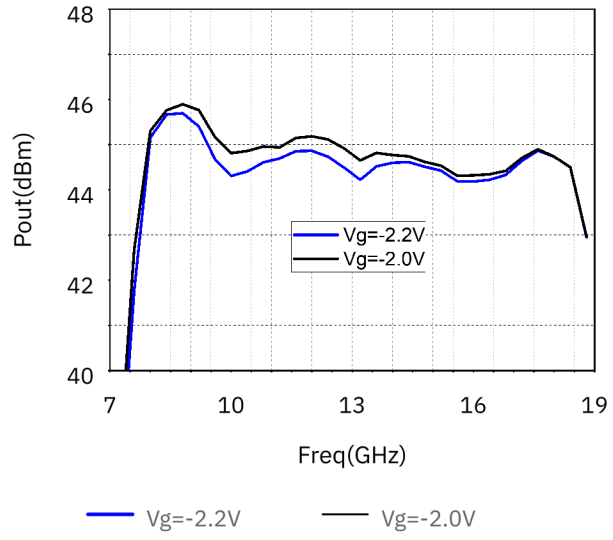


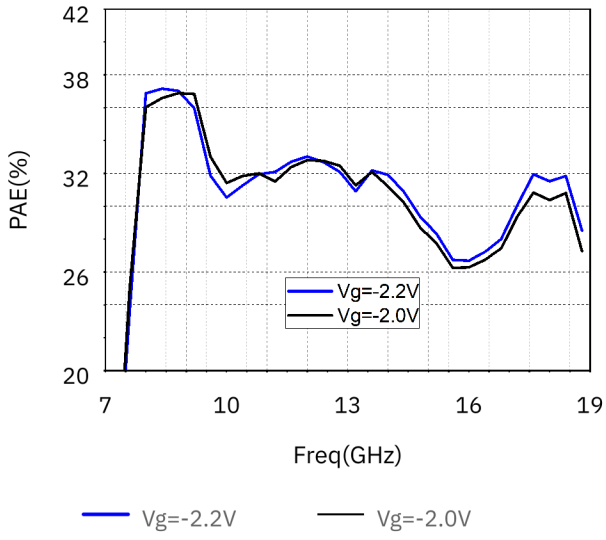


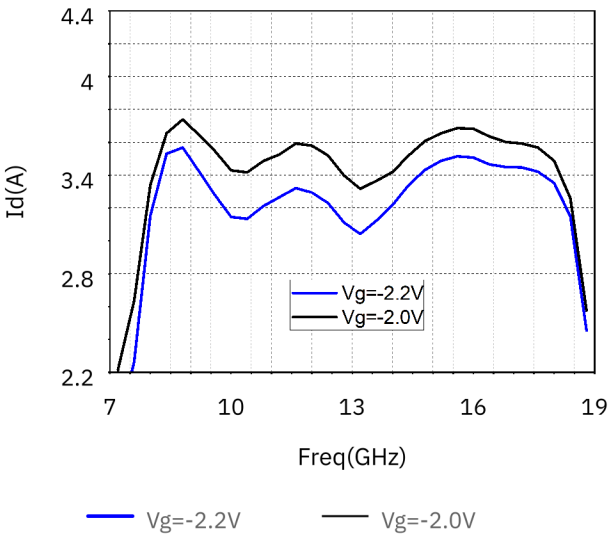


Continuous wave (CW) — Saturated output power; Power-added efficiency; Dynamic drain current.

Figure notes: TA=+25°C; Vd=+28V; Pin=25dBm. Vg = -2.2/-2.0 V.







Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.